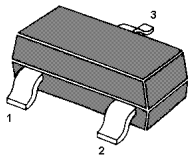
MMBTSA2018

PNP Silicon Epitaxial Planar Transistor

Low Frequency Transistor
for switching and muting applications.



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Features:

- A collector current is large.
- Collector saturation voltage is low.
  $-V_{CE(sat)}$: 250mV(Max.) at $-I_C$=200mA/$-I_B$=10mA

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	15	V
Collector Emitter Voltage	$-V_{CEO}$	12	V
Collector Current	$-I_C$	500	mA
	$-I_{CP}$ [1)]	1	A
Collector Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{Stg}	-55 to +150	°C

[1)] Single pulse, P_W=1ms

Characteristics at T_{amb}=25 °C

	Symbol	Min.	Typ.	Max.	Unit
DC Current Transfer Ratio at $-I_C$=10mA, $-V_{CE}$=2V	h_{FE}	270	-	680	-
Collector Cutoff Current at $-V_{CB}$=15V	$-I_{CBO}$	-	-	100	nA
Collector Base Breakdown Voltage at $-I_C$=10μA	$-V_{(BR)CBO}$	15	-	-	V
Collector Emitter Breakdown Voltage at $-I_C$=1mA	$-V_{(BR)CEO}$	12	-	-	V
Emitter Base Breakdown Voltage at $-I_E$=10μA	$-V_{(BR)EBO}$	6	-	-	V
Collector Emitter Saturation Voltage at $-I_C$=200mA, $-I_B$=10mA	$-V_{CE(sat)}$	-	-	250	mV
Transition Frequency at $-V_{CE}$=2V, $-I_E$=10mA, f=100MHz	f_T	-	260	-	MHz
Output Capacitance at $-V_{CB}$=10V, f=1MHz	C_{ob}	-	6.5	-	pF